

## **80V PNP SMALL SIGNAL TRANSISTOR IN SOT323**

#### **Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

#### **Features**

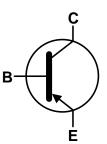
- BV<sub>CEO</sub> > -80V
- I<sub>C</sub> = -500mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMSTA06Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

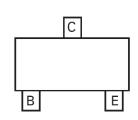
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound.
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)







Device Symbol



Pin-out Top View

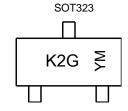
#### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMSTA56Q-7-F	Automotive	K2G	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



K2G = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	2	2016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	E	F	G	Н		,	J	K	L	М
Monti	n	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	)	1	2	3	4	5	6	7	8	9	0	N	D



#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	V
Emitter-Base Voltage	V <sub>EBO</sub>	-4	V
Collector Current	Ic	-500	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

## **Thermal Characteristics and Derating Information**

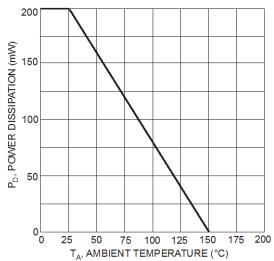


Fig. 1 Max Power Dissipation vs. Ambient Temperature

<sup>6.</sup> For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>7.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Electrical Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-80	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-80	_	V	I <sub>C</sub> = -1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-4	_	V	I <sub>E</sub> = -100μA
Collector Base Cutoff Current	I <sub>CBO</sub>		-100	nA	$V_{CB} = -80V, T_A = +125^{\circ}C$
Collector Cutoff Current	I <sub>CEX</sub>	_	-100	nA	V <sub>CE</sub> = -80V
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h	100			$I_C = -10 \text{mA}, V_{CE} = -1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	_		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-0.25	V	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		-1.2	V	$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f⊤	50		MHz	$V_{CE} = -1.0V, I_{C} = -100mA,$
Ourient Gain Bandwidth i roddet	''	30		1011 12	f = 100MHz

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

#### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

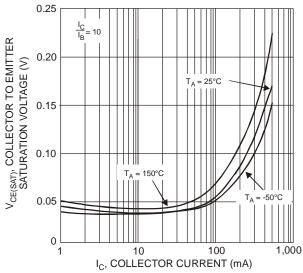


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

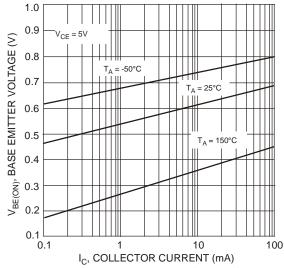


Fig. 4 Base Emitter Voltage vs. Collector Current

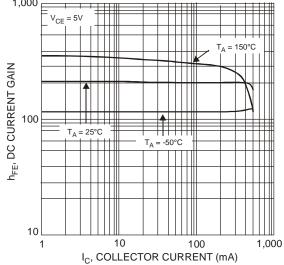


Fig. 3, DC Current Gain vs. Collector Current

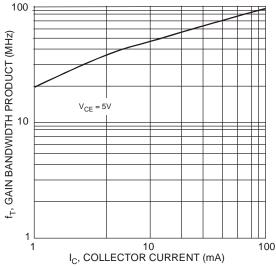
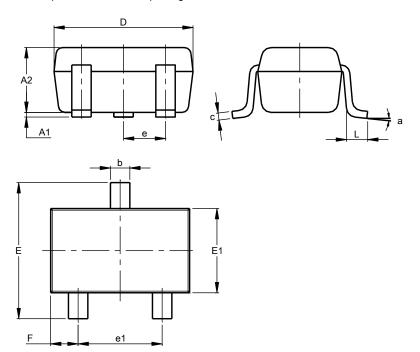


Fig. 5 Gain Bandwidth Product vs. Collector Current



## **Package Outline Dimensions**

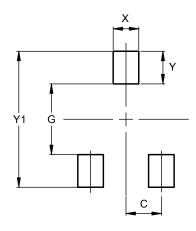
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
C	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value
פווטופווסוטווס	(in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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